

# 7MBR50VW120-50

## IGBT MODULE (V series)

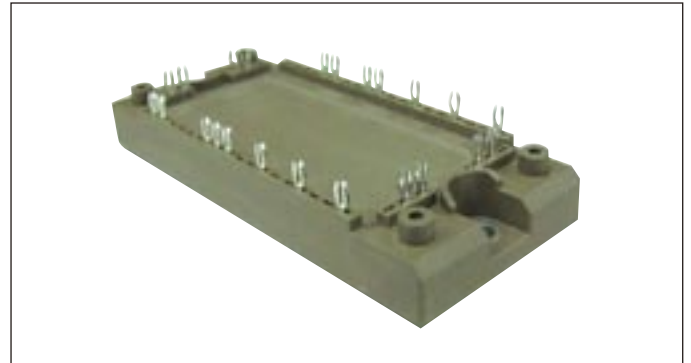
### 1200V / 50A / PIM

#### ■ Features

- Low  $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant product

#### ■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply



#### ■ Maximum Ratings and Characteristics

##### ● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	$V_{CES}$	1200	V	
	Gate-Emitter voltage	$V_{GES}$	$\pm 20$	V	
	Collector current	$I_c$	Continuous $T_c=80^\circ\text{C}$	50	A
		$I_{cp}$	1ms $T_c=80^\circ\text{C}$	100	
		$-I_c$		50	
		$-I_c$ pulse	1ms	100	
Collector power dissipation	$P_c$	1 device	280	W	
Brake	Collector-Emitter voltage	$V_{CES}$	1200	V	
	Gate-Emitter voltage	$V_{GES}$	$\pm 20$	V	
	Collector current	$I_c$	Continuous $T_c=80^\circ\text{C}$	35	A
		$I_{cp}$	1ms $T_c=80^\circ\text{C}$	70	
	Collector power dissipation	$P_c$	1 device	210	W
Repetitive peak reverse voltage (Diode)	$V_{RRM}$		1200	V	
Converter	Repetitive peak reverse voltage	$V_{RRM}$	1600	V	
	Average output current	$I_o$	50Hz/60Hz, sine wave	50	A
	Surge current (Non-Repetitive)	$I_{FSM}$	10ms, $T_j=150^\circ\text{C}$	360	A
	$I^2t$ (Non-Repetitive)	$I^2t$	half sine wave	648	$\text{A}^2\text{s}$
Junction temperature	$T_j$	Inverter, Brake	175	$^\circ\text{C}$	
		Converter	150		
Operating junction temperature (under switching conditions)	$T_{jop}$	Inverter, Brake	150		
		Converter	150		
Case temperature	$T_c$		125		
Storage temperature	$T_{stg}$		-40 to +125		
Isolation voltage	between terminal and copper base (*1) between thermistor and others (*2)	$V_{iso}$	AC : 1min.	VAC	
Screw torque	Mounting (*3)	-	M5	N m	

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable value : 2.5-3.5 Nm (M5)

● Electrical characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units		
			min.	typ.	max.			
Inverter	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>GE</sub> = 0V, V <sub>GE</sub> = ±20V	-	-	200	nA	
	Gate-Emitter threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = 20V, I <sub>c</sub> = 50mA	6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>c</sub> = 50A	T <sub>j</sub> = 25°C	-	2.20	2.65	V
				T <sub>j</sub> = 125°C	-	2.55	-	
				T <sub>j</sub> = 150°C	-	2.60	-	
		V <sub>CE(sat)</sub> (chip)	V <sub>GE</sub> = 15V I <sub>c</sub> = 50A	T <sub>j</sub> = 25°C	-	1.85	2.30	
				T <sub>j</sub> = 125°C	-	2.20	-	
	T <sub>j</sub> = 150°C	-	2.25	-				
	Input capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz	-	4.2	-	nF	
	Turn-on time	ton	V <sub>CC</sub> = 600V I <sub>c</sub> = 50A V <sub>GE</sub> = +15 / -15V R <sub>G</sub> = 15Ω	-	0.39	1.20	μs	
		tr		-	0.09	0.60		
		tr(i)		-	0.03	-		
	Turn-off time	toff	R <sub>G</sub> = 15Ω	-	0.53	1.00	μs	
		tf		-	0.06	0.30		
Forward on voltage	V <sub>F</sub> (terminal)	I <sub>F</sub> = 50A	T <sub>j</sub> = 25°C	-	2.25	2.70	V	
			T <sub>j</sub> = 125°C	-	2.50	-		
			T <sub>j</sub> = 150°C	-	2.45	-		
	V <sub>F</sub> (chip)	I <sub>F</sub> = 50A	T <sub>j</sub> = 25°C	-	1.90	2.35		
			T <sub>j</sub> = 125°C	-	2.15	-		
T <sub>j</sub> = 150°C	-	2.10	-					
Reverse recovery time	trr	I <sub>F</sub> = 50A	-	-	0.1	μs		
Brake	Zero gate voltage collector current	I <sub>CES</sub>	V <sub>GE</sub> = 0V V <sub>CE</sub> = 1200V	-	-	1.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	V <sub>CE</sub> = 0V V <sub>GE</sub> = +20 / -20V	-	-	200	nA	
	Collector-Emitter saturation voltage	V <sub>CE(sat)</sub> (terminal)	V <sub>GE</sub> = 15V I <sub>c</sub> = 35A	T <sub>j</sub> = 25°C	-	2.10	2.55	V
				T <sub>j</sub> = 125°C	-	2.45	-	
				T <sub>j</sub> = 150°C	-	2.50	-	
		V <sub>CE(sat)</sub> (chip)	V <sub>GE</sub> = 15V I <sub>c</sub> = 35A	T <sub>j</sub> = 25°C	-	1.85	2.30	
				T <sub>j</sub> = 125°C	-	2.20	-	
	T <sub>j</sub> = 150°C	-	2.25	-				
	Turn-on time	ton	V <sub>CE</sub> = 600V I <sub>c</sub> = 35A V <sub>GE</sub> = +15 / -15V R <sub>G</sub> = 27Ω	-	0.39	1.20	μs	
		tr		-	0.09	0.60		
Turn-off time	toff	R <sub>G</sub> = 27Ω	-	0.53	1.00	μs		
	tf		-	0.06	0.30			
Reverse current	IRRM	V <sub>R</sub> = 1200V	-	-	1.00	mA		
Converter	Forward on voltage	I <sub>F</sub> = 50A	terminal	-	1.70	2.05	V	
			chip	-	1.35	-		
Reverse current	IRRM	V <sub>R</sub> = 1600V	-	-	1.0	mA		
Thermistor	Resistance	T = 25°C	-	5000	-	Ω		
		T = 100°C	465	495	520			
B value	B	T = 25 / 50°C	3305	3375	3450	K		

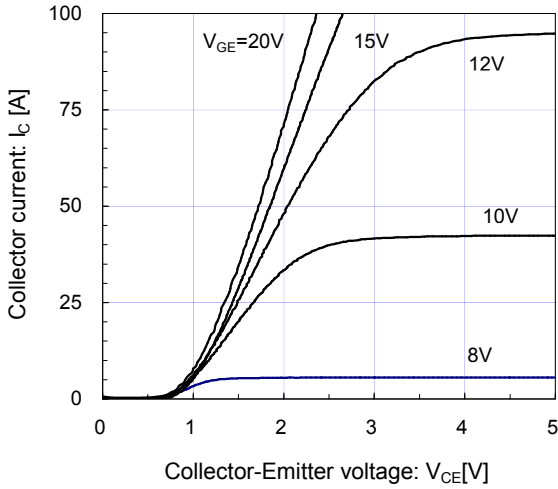
## ● Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R <sub>th(j-c)</sub>	Inverter IGBT	-	-	0.54	°C/W
		Inverter FWD	-	-	0.91	
		Brake IGBT	-	-	0.72	
		Converter Diode	-	-	0.54	
Contact thermal resistance (1device) (*4)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.05	-	

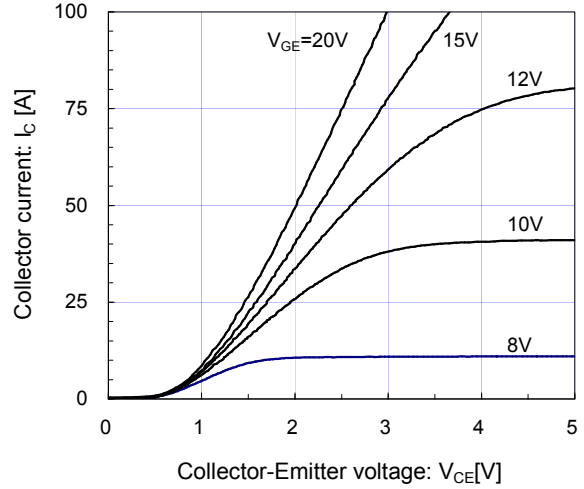
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

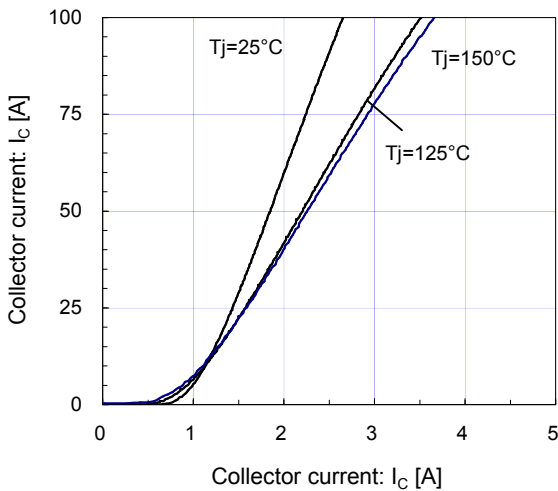
[ Inverter ]  
 Collector current vs. Collector-Emmitter voltage (typ.)  
 $T_j = 25^\circ\text{C}$  / chip



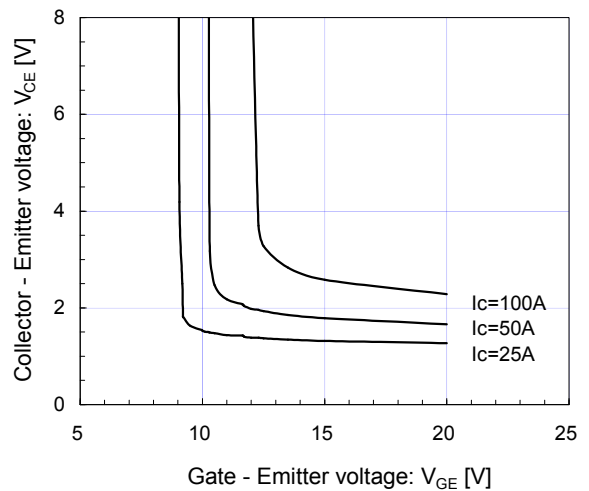
[ Inverter ]  
 Collector current vs. Collector-Emmitter voltage (typ.)  
 $T_j = 150^\circ\text{C}$  / chip



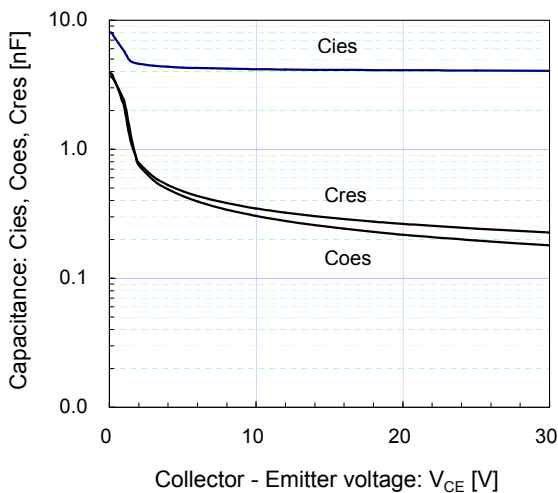
[ Inverter ]  
 Collector current vs. Collector-Emmitter voltage (typ.)  
 $V_{GE} = 15\text{V}$  / chip



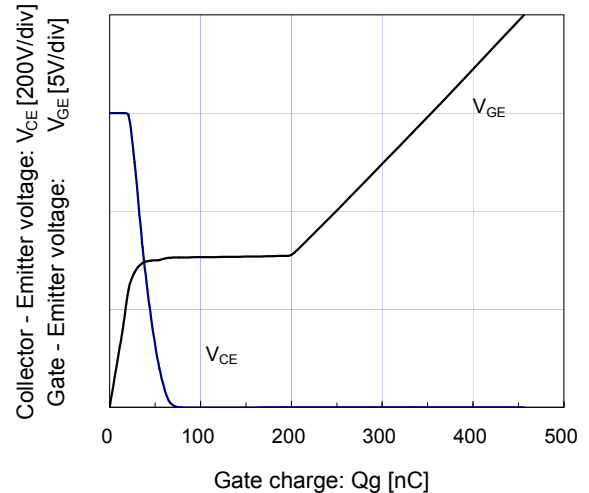
[ Inverter ]  
 Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)  
 $T_j = 25^\circ\text{C}$  / chip



[ Inverter ]  
 Capacitance vs. Collector-Emmitter voltage (typ.)  
 $V_{GE} = 0\text{V}$ ,  $f = 1\text{MHz}$ ,  $T_j = 25^\circ\text{C}$

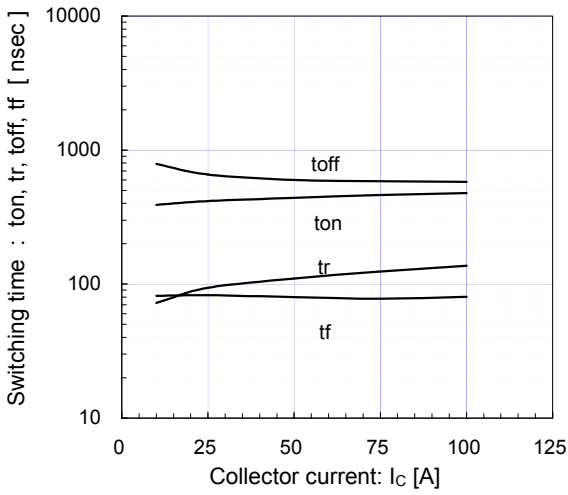


[ Inverter ]  
 Dynamic gate charge (typ.)  
 $V_{CC} = 600\text{V}$ ,  $I_c = 50\text{A}$ ,  $T_j = 25^\circ\text{C}$



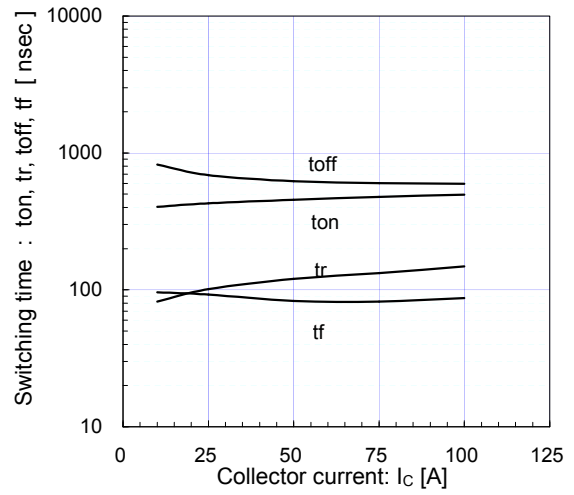
[ Inverter ]

Switching time vs. Collector current (typ.)  
 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=15\Omega, T_j=125^\circ C$



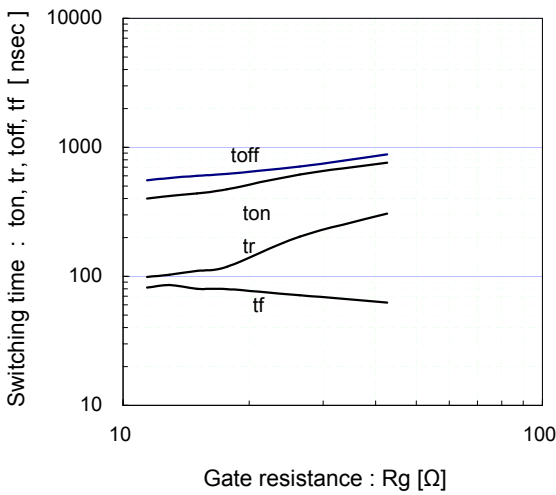
[ Inverter ]

Switching time vs. Collector current (typ.)  
 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=15\Omega, T_j=150^\circ C$



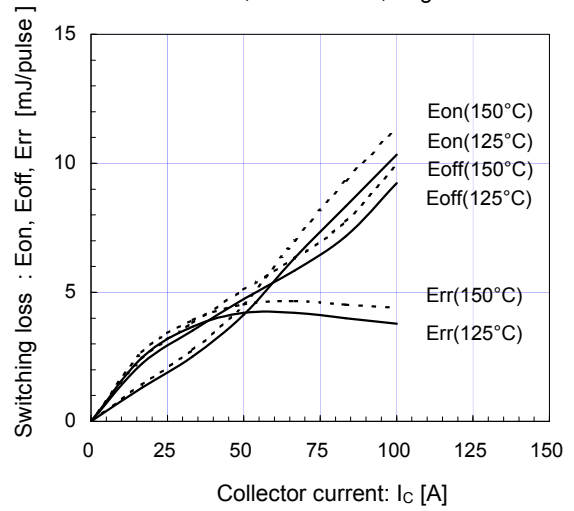
[ Inverter ]

Switching time vs. gate resistance (typ.)  
 $V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V, T_j=125^\circ C$



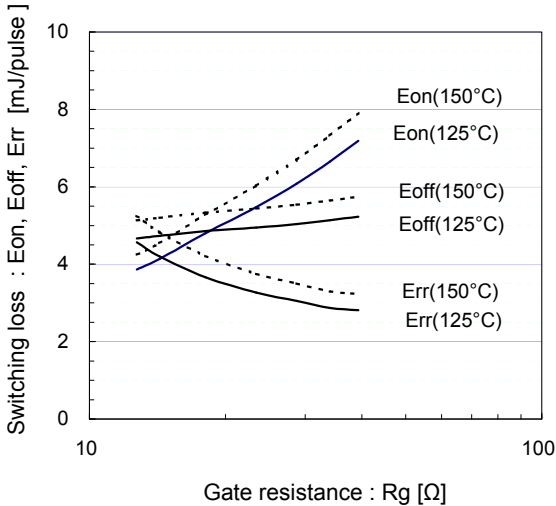
[ Inverter ] a

Switching loss vs. Collector current (typ.)  
 $V_{cc}=600V, V_{GE}=\pm 15V, R_g=15\Omega$



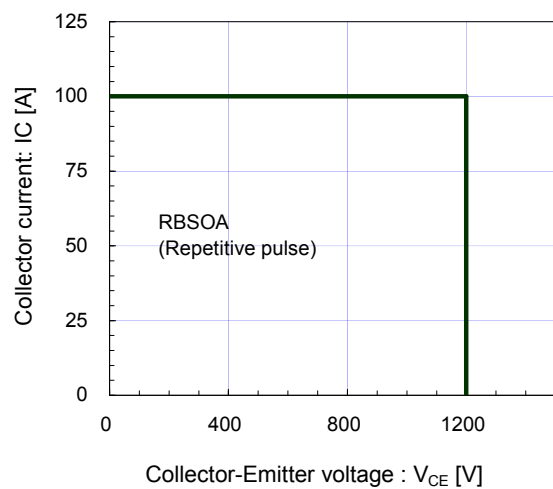
[ Inverter ]

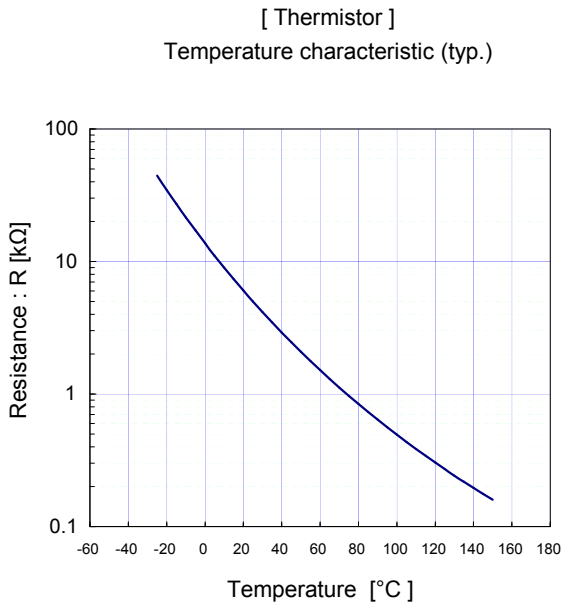
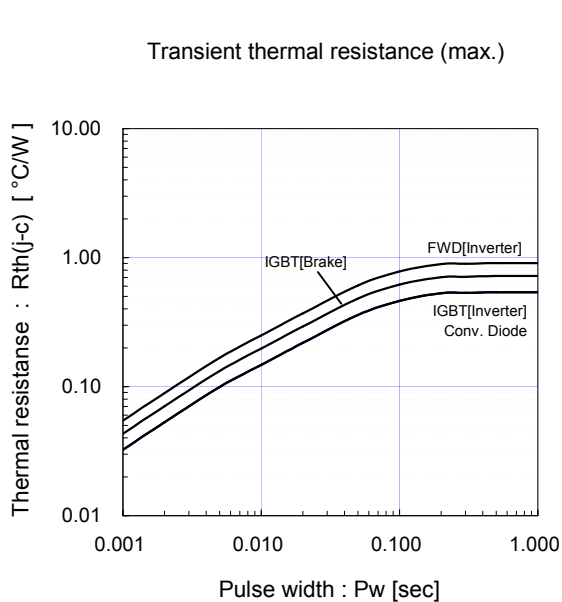
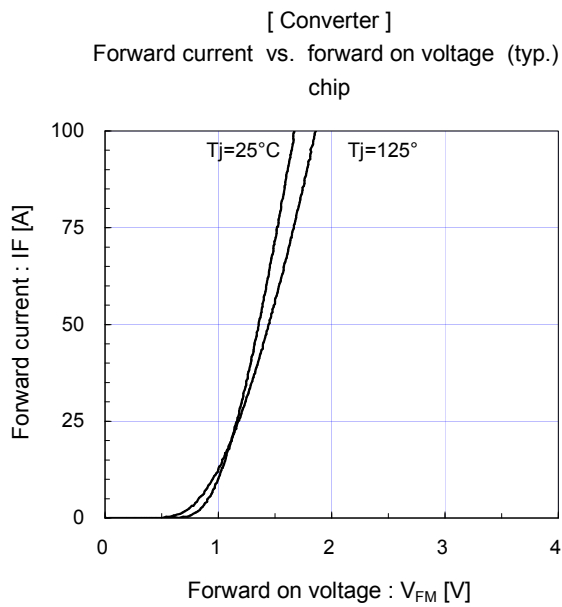
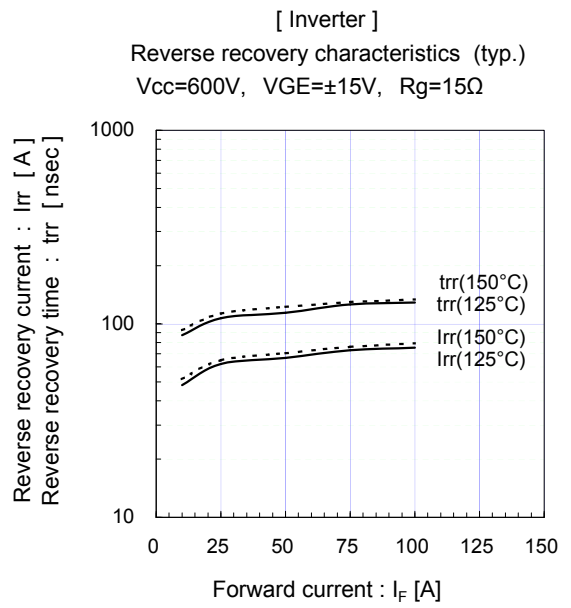
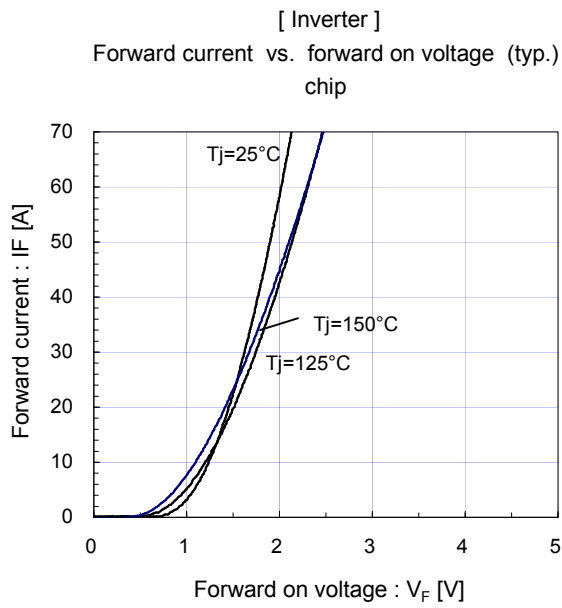
Switching loss vs. gate resistance (typ.)  
 $V_{cc}=600V, I_c=50A, V_{GE}=\pm 15V$



[ Inverter ]

Reverse bias safe operating area (max.)  
 $+V_{GE}=15V, -V_{GE} \leq 15V, R_g \geq 15\Omega, T_j \leq 125^\circ C$

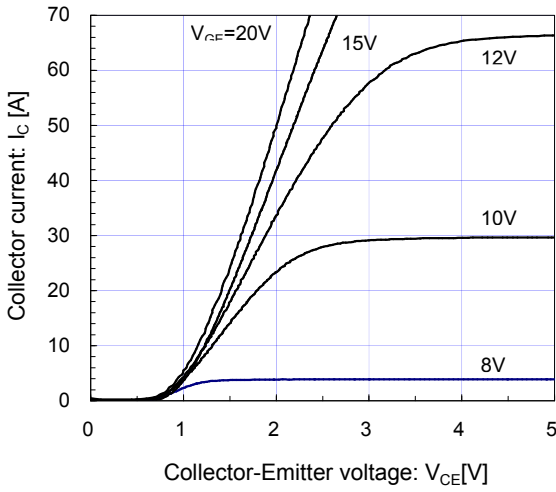




[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

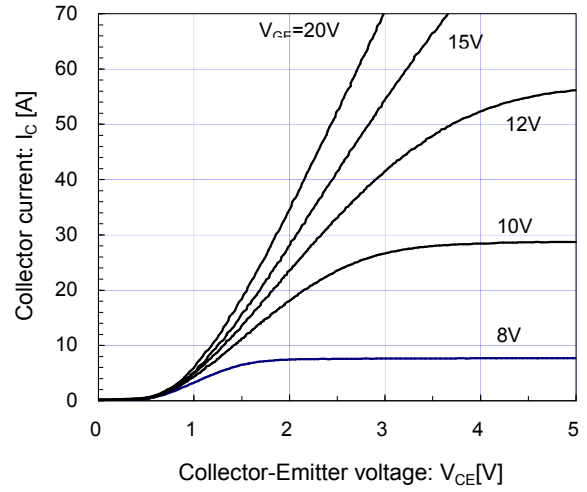
T<sub>j</sub> = 25°C / chip



[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

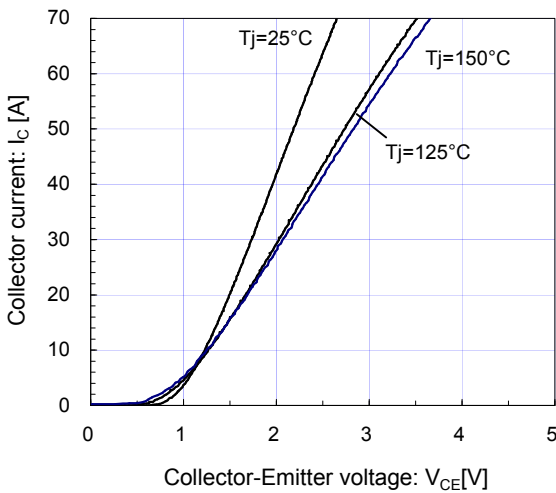
T<sub>j</sub> = 150°C / chip



[ Brake ]

Collector current vs. Collector-Emmitter voltage (typ.)

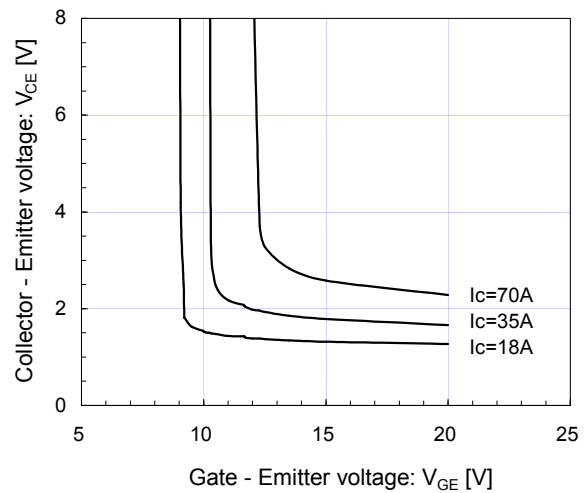
V<sub>GE</sub> = 15V / chip



[ Brake ]

Collector-Emmitter voltage vs. Gate-Emmitter voltage (typ.)

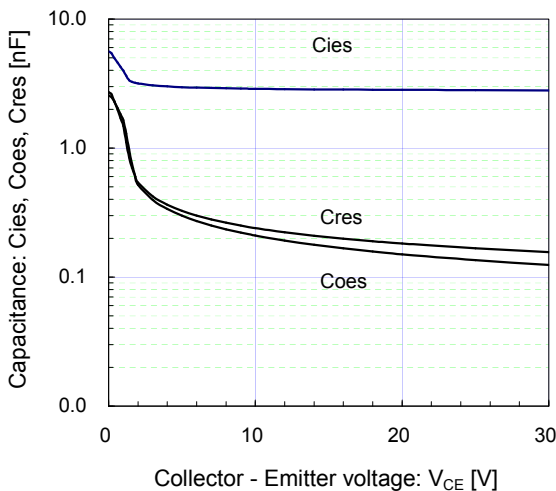
T<sub>j</sub> = 25°C / chip



[ Brake ]

Capacitance vs. Collector-Emmitter voltage (typ.)

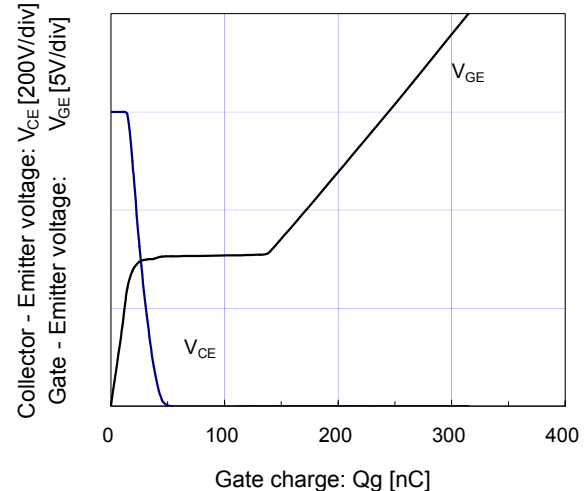
V<sub>GE</sub> = 0V, f = 1MHz, T<sub>j</sub> = 25°C



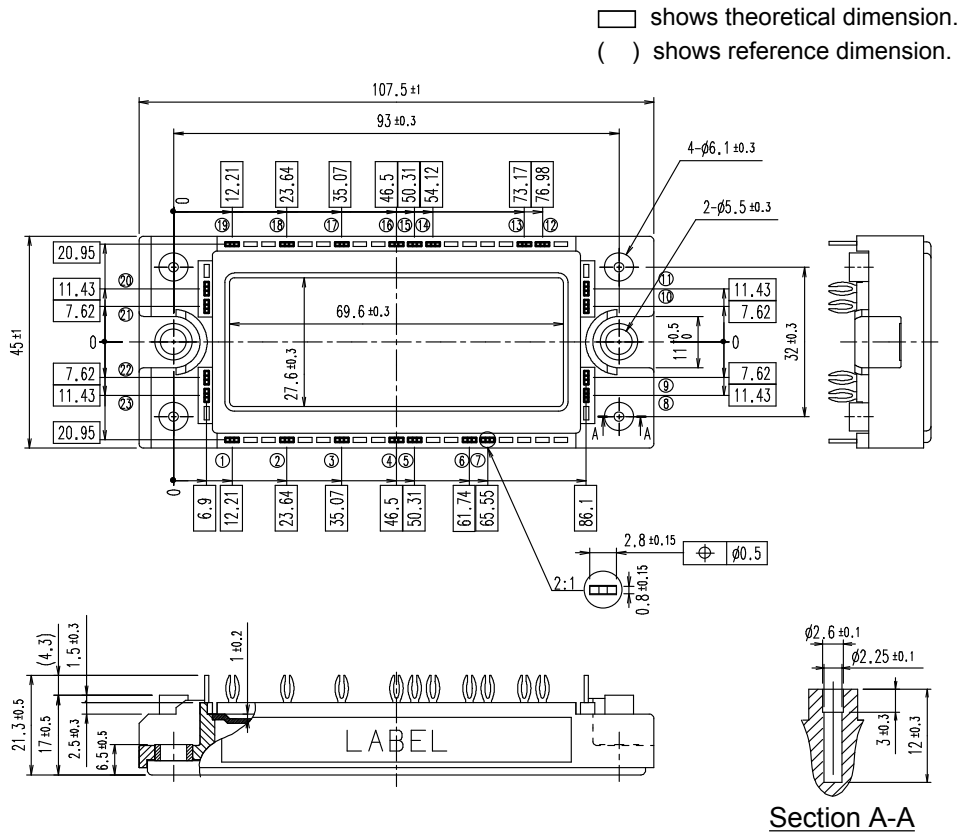
[ Brake ]

Dynamic gate charge (typ.)

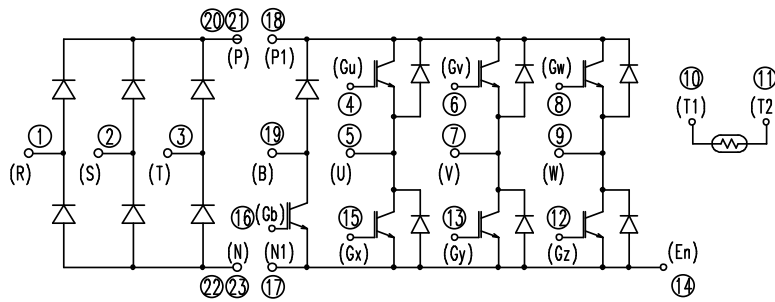
V<sub>CC</sub> = 600V, I<sub>C</sub> = 50A, T<sub>j</sub> = 25°C



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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